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		INFORMATION DISCLOSURE STATEMENT BY APPLICANT (Use several sheets if necessary)	
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		YUGAMI et al	
		FILING DATE	GROUP
		December 7, 2001	Unassigned

## U.S. PATENT DOCUMENTS

Examiner Initial	Document Number	Date	Name	Class	Subclass	Filing Date
	AA					
	AB					
	AC					
	AD					
	AE					
	AF					
	AG					
	AH					
	AI					
	AJ					
	AK					
	AL					

## FOREIGN PATENT DOCUMENTS

Examiner Initial	Document Number	Date	Country	Class	Subclass	Translation	
						Yes	No
SBG	AM	110003990	1/6/99	JAPAN			X
	AN						
	AO						
	AP						
	AQ						
	AR						
	AS						
	AT						

## OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)

SBG	AU	1998 International Electron Device Meeting Technical Digest, (Pgs. 1038-1040), A 1.1 nm Oxide Equivalent Gate Insulator Formed Using TiO <sub>2</sub> on Nitrided Silicon.					
SBG	AV	IEEE Transactions on Electron Devices, Vol. 46, No. 7, July 1999, (Pages 1537-1544), The Impact of High-k Gate Dielectrics and Metal Gate Electrodes on Sub-100 nm MOSFET's					
	AW						
	AX						
	AY						
	AZ						
Examiner				Date Considered			
Det. P. Ky				4-15-03			

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